

E Series Power MOSFET

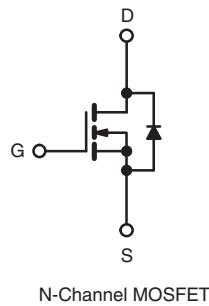
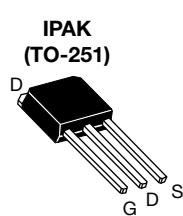
PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	700
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V 0.9
Q_g max. (nC)	34
Q_{gs} (nC)	4
Q_{gd} (nC)	8
Configuration	Single

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

ORDERING INFORMATION	
Package	IPAK (TO-251)
Lead (Pb)-free and Halogen-free	SiHU6N62E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	620	V
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	I_D	6	A
	$T_C = 25$ °C		4	
Pulsed Drain Current ^a		I_{DM}	12	
Linear Derating Factor			0.63	W/°C
Single Pulse Avalanche Energy ^b		E_{AS}	88	mJ
Maximum Power Dissipation		P_D	78	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	$T_J = 125$ °C	dV/dt	37	V/ns
Reverse Diode dV/dt ^d			12	
Soldering Recommendations (Peak Temperature) ^c	for 10 s		300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω, $I_{AS} = 2.5$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/μs, starting $T_J = 25$ °C.

THERMAL RESISTANCE RATINGS

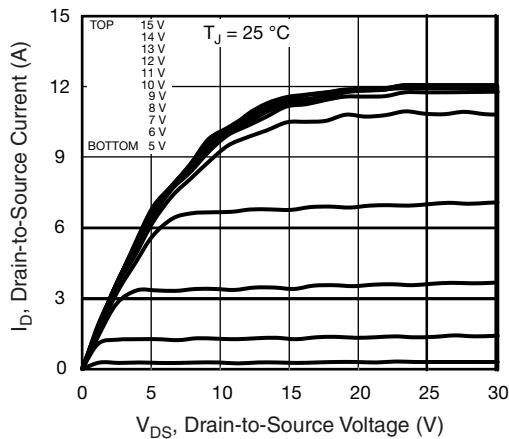
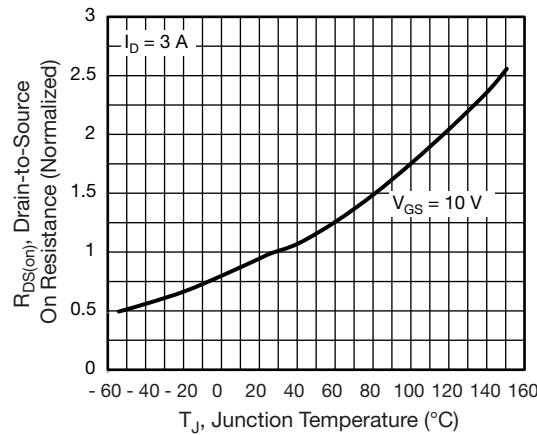
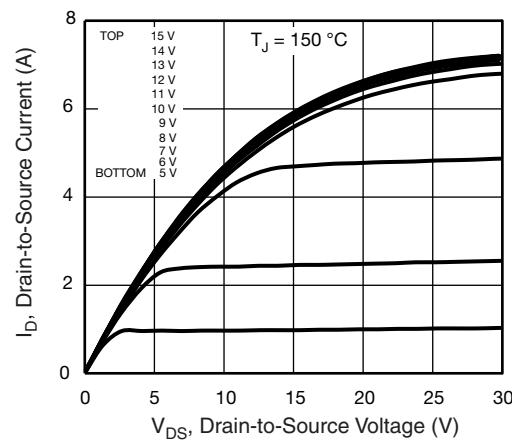
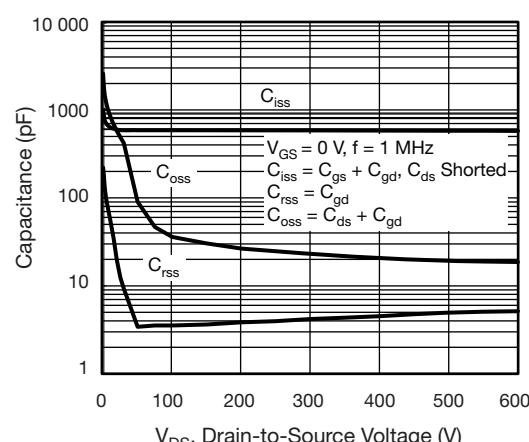
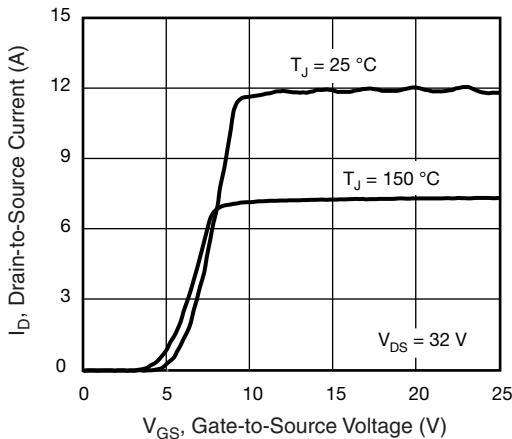
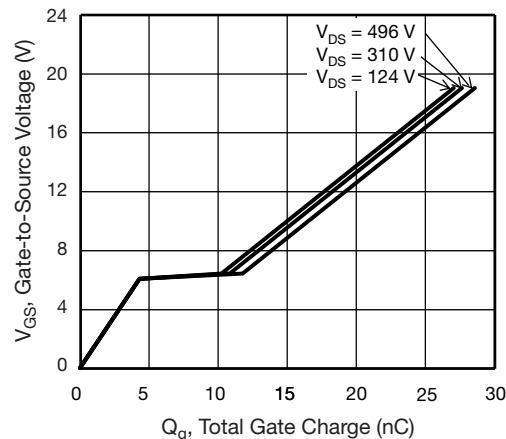
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	$^{\circ}\text{C}/\text{W}$
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.6	

SPECIFICATIONS ($T_J = 25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$	$I_D = 250 \mu\text{A}$	620	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1 \text{ mA}$		-	0.76	-	$^{\circ}\text{C}/\text{V}$	
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		2	-	4	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		$V_{GS} = \pm 30 \text{ V}$		-	-	± 1	μA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 620 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	1	μA	
		$V_{DS} = 496 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^{\circ}\text{C}$		-	-	10		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 3 \text{ A}$	-	0.78	0.90	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 30 \text{ V}$, $I_D = 3 \text{ A}$		-	1.8	-	S	
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 100 \text{ V}$, $f = 1 \text{ MHz}$		-	578	-	pF	
Output Capacitance	C_{oss}			-	36	-		
Reverse Transfer Capacitance	C_{rss}			-	4	-		
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0 \text{ V}$ to 496 V , $V_{GS} = 0 \text{ V}$		-	31	-		
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	87	-		
Total Gate Charge	Q_g			-	17	34	nC	
Gate-Source Charge	Q_{gs}	$V_{GS} = 10 \text{ V}$	$I_D = 3 \text{ A}$, $V_{DS} = 496 \text{ V}$	-	4	-		
Gate-Drain Charge	Q_{gd}			-	8	-		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 496 \text{ V}$, $I_D = 3 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_g = 9.1 \Omega$		-	12	24	ns	
Rise Time	t_r			-	10	20		
Turn-Off Delay Time	$t_{d(off)}$			-	22	44		
Fall Time	t_f			-	16	32		
Gate Input Resistance	R_g	$f = 1 \text{ MHz}$, open drain		-	1.3	-	Ω	
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	7	A	
Pulsed Diode Forward Current	I_{SM}			-	-	12		
Diode Forward Voltage	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_S = 3 \text{ A}$, $V_{GS} = 0 \text{ V}$		-	0.9	1.2	V	
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}$, $I_F = I_S = 3 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}$, $V_R = 400 \text{ V}$		-	190	-	ns	
Reverse Recovery Charge	Q_{rr}			-	1.3	-		
Reverse Recovery Current	I_{RRM}			-	11	-		

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

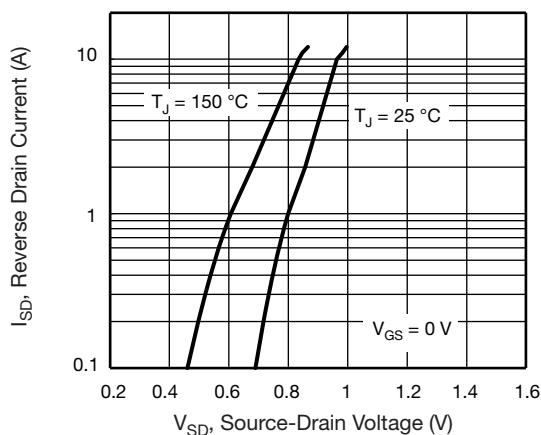


Fig. 7 - Typical Source-Drain Diode Forward Voltage

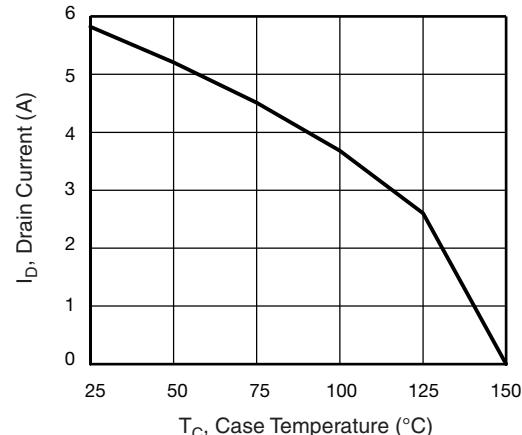


Fig. 9 - Maximum Drain Current vs. Case Temperature

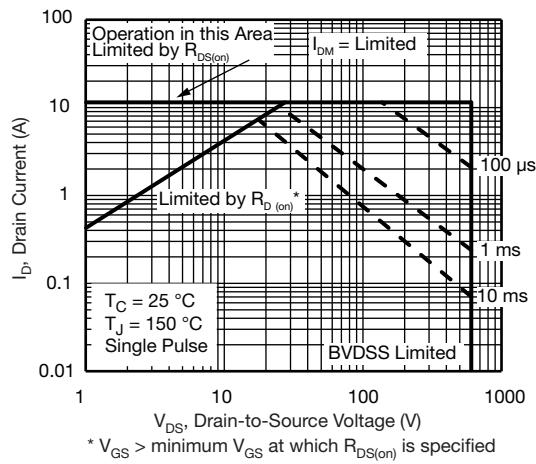


Fig. 8 - Maximum Safe Operating Area

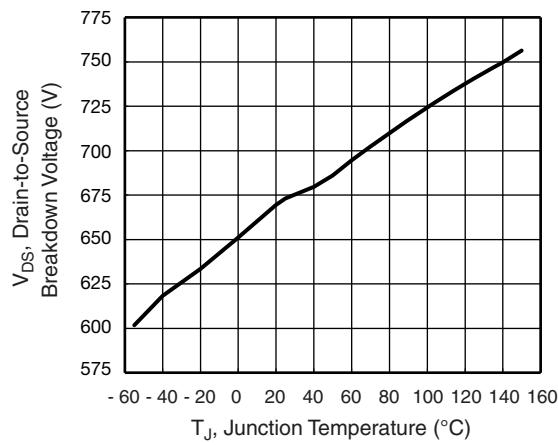


Fig. 10 - Temperature vs. Drain-to-Source Voltage

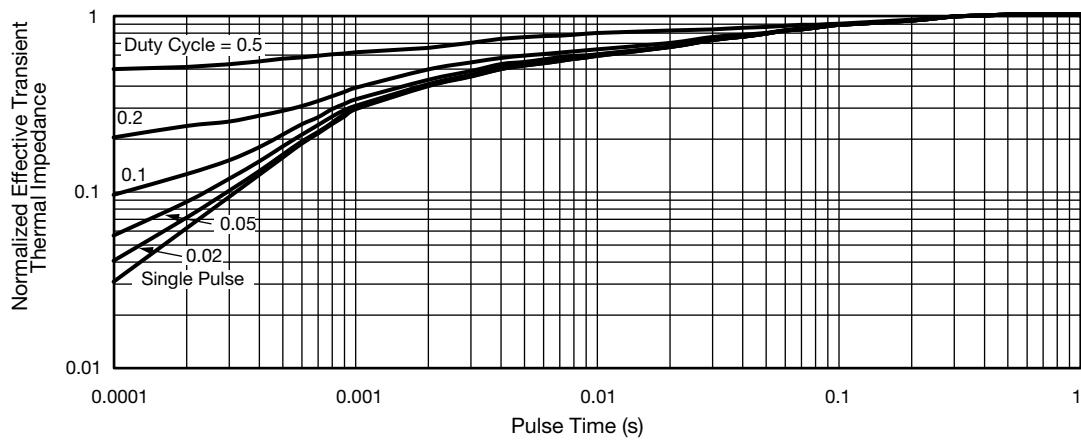
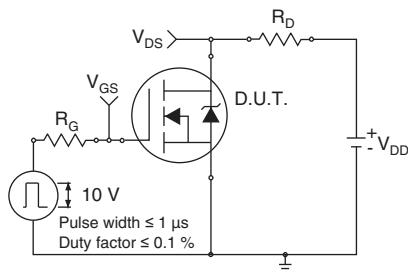
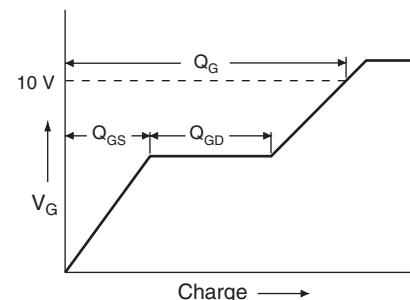
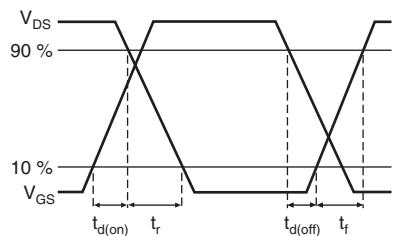
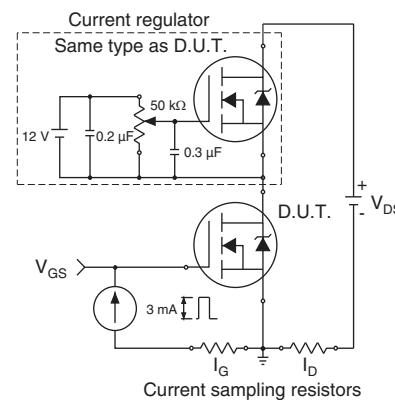
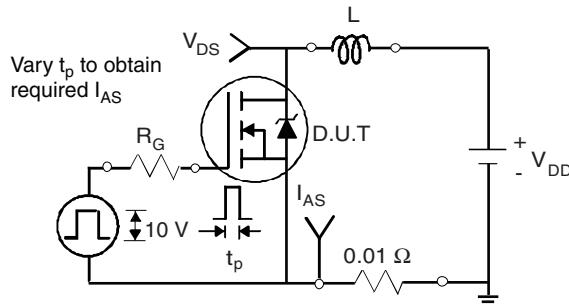
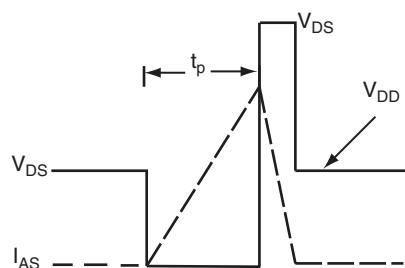
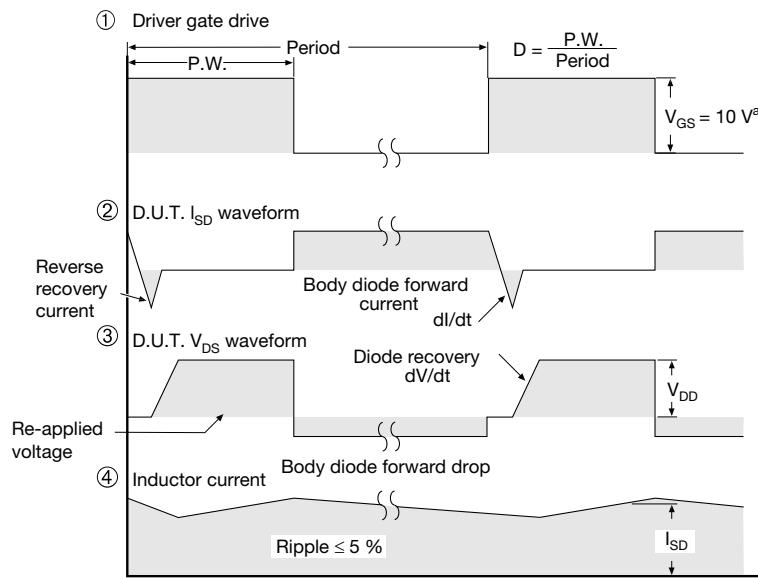
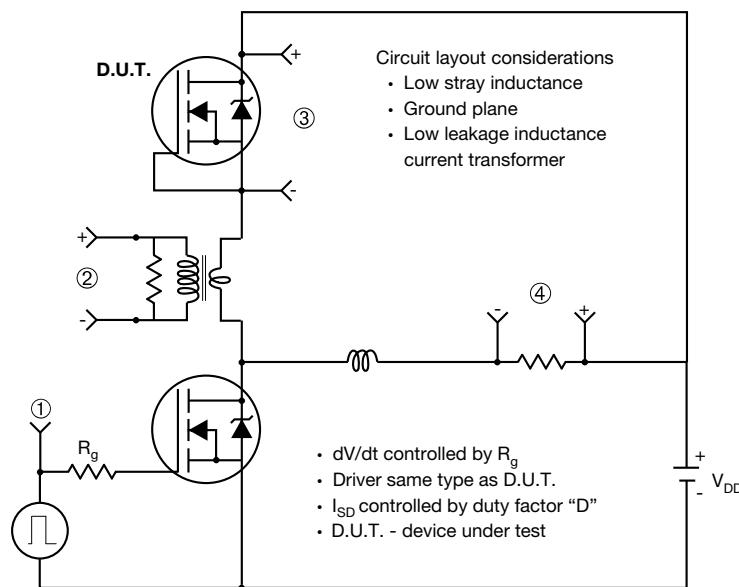


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

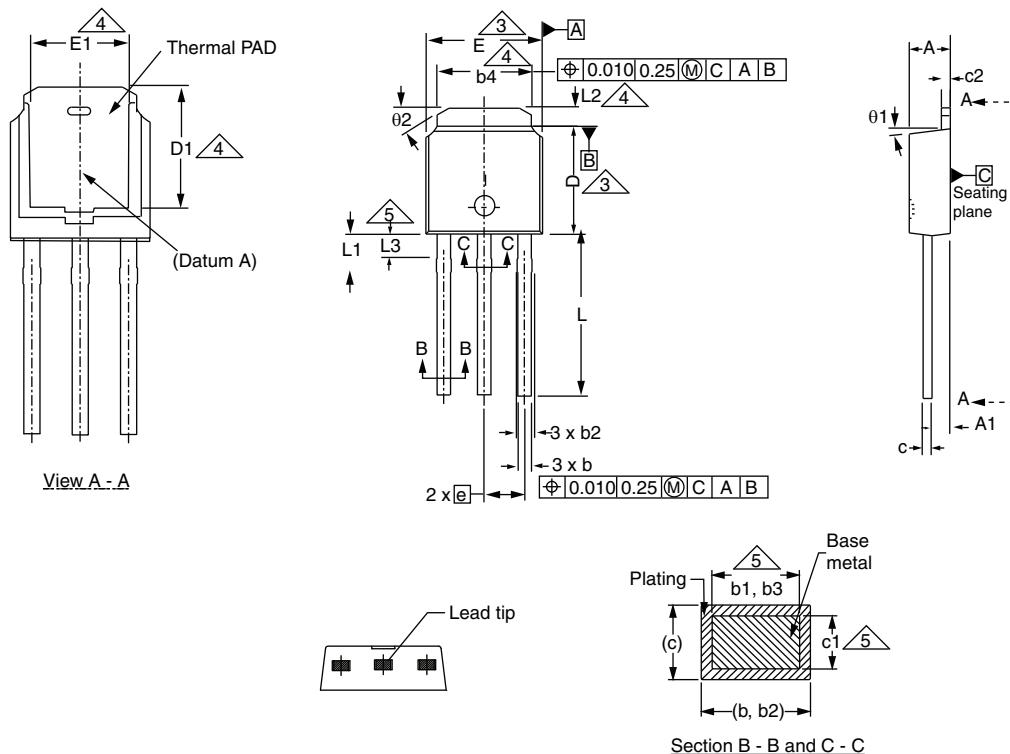

Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

Fig. 13 - Switching Time Waveforms

Fig. 17 - Gate Charge Test Circuit

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery dV/dt Test Circuit

Fig. 18 - For N-Channel

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Case Outline for TO-251AA (High Voltage)

OPTION 1:



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

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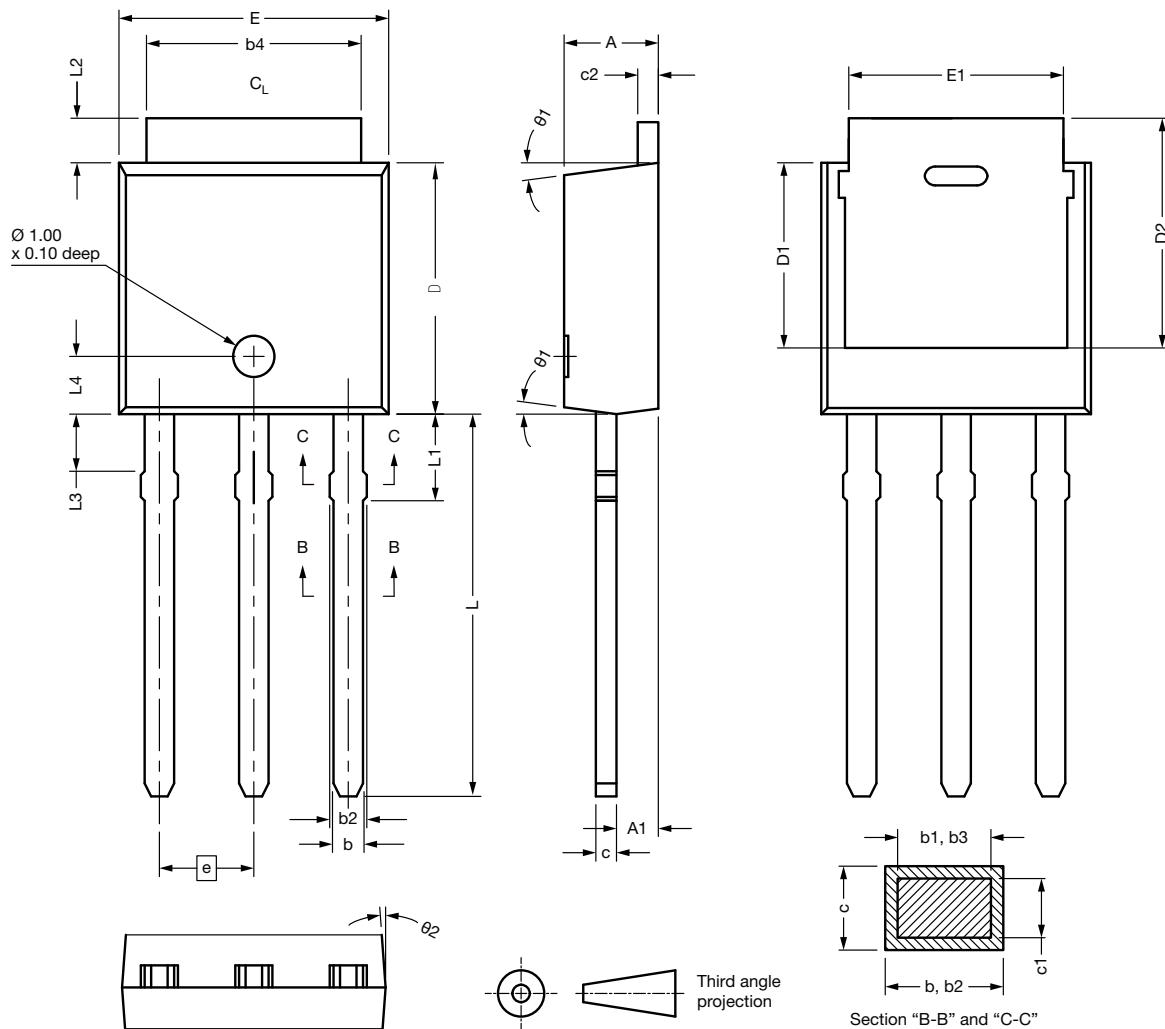
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	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
01	0'	15'	0'	15'
02	25'	35'	25'	35'

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension are shown in inches and millimeters
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions b4, L2, E1 and D1
- Lead dimension uncontrolled in L3
- Dimension b1, b3 and c1 apply to base metal only
- Outline conforms to JEDEC® outline TO-251AA

OPTION 2: FACILITY CODE = N



DIM.	MIN.	NOM.	MAX.
A	2.180	2.285	2.390
A1	0.890	1.015	1.140
b	0.640	0.765	0.890
b1	0.640	0.715	0.790
b2	0.760	0.950	1.140
b3	0.760	0.900	1.040
b4	4.950	5.205	5.460
c	0.460	-	0.610
c1	0.410	-	0.560
c2	0.460	-	0.610
D	5.970	6.095	6.220
D1	4.300	-	-

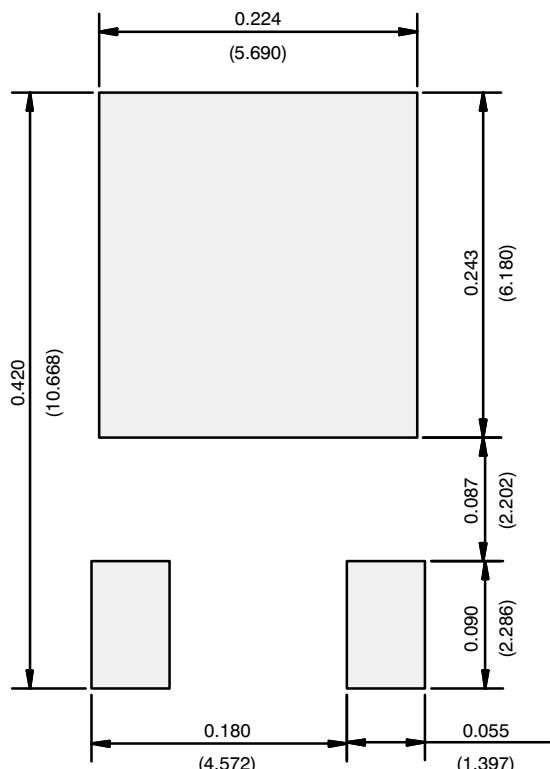
DIM.	MIN.	NOM.	MAX.
D2	5.380	-	-
E	6.350	6.540	6.730
E1	4.32	-	-
e	2.29 BSC		
L	8.890	9.270	9.650
L1	1.910	2.100	2.290
L2	0.890	1.080	1.270
L3	1.140	1.330	1.520
L4	1.300	1.400	1.500
01	0°	7.5°	15°
02	4°	-	-

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DWG: 5968

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- All dimension are in millimeters, angles are in degrees
- Heat sink side flash is max. 0.8 mm

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)

Recommended Minimum Pads
Dimensions in Inches/(mm)

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